Xiao-Di Huang

List of Publications by Year
in descending order

11 papers	308 citations	1040056 9 h-index	1372567 10 g-index
11 all docs	11 docs citations	11 times ranked	299 citing authors

#	Article	IF	Citations
1	Pt/Al_2O_3/TaO$_X$/Ta Self-Rectifying Memristor With Record-Low Operation Current (<2 pA), Low Power (fJ), and High Scalability. IEEE Transactions on Electron Devices, 2022, 69, 838-842.	3.0	11
2	Reconfigurable Synaptic and Neuronal Functions in a V/VO$_x$/HfWO$_x$/Pt Memristor for Nonpolar Spiking Convolutional Neural Network. Advanced Functional Materials, 2022, 32, .	14.9	25
3	12.7 MA/cm^2 On-Current Density and High Uniformity Realized in AgGeSe/Al_2O_3 Selectors. IEEE Electron Device Letters, 2021, 42, 613-616.	3.9	4
4	Low‑Power Memristive Logic Device Enabled by Controllable Oxidation of 2D $HfSe_2$ for In‑Memory Computing. Advanced Science, 2021, 8, e2005038.	11.2	47
5	Controlled Majority-Inverter Graph Logic With Highly Nonlinear, Self-Rectifying Memristor. IEEE Transactions on Electron Devices, 2021, 68, 4897-4902.	3.0	12
6	Controlled Memory and Threshold Switching Behaviors in a Heterogeneous Memristor for Neuromorphic Computing. Advanced Electronic Materials, 2020, 6, 2000309.	5.1	38
7	Low-Power Artificial Neurons Based on Ag/TiN/HfAlOx/Pt Threshold Switching Memristor for Neuromorphic Computing. IEEE Electron Device Letters, 2020, 41, 1245-1248.	3.9	58
8	Design of High Robustness BNN Inference Accelerator Based on Binary Memristors. IEEE Transactions on Electron Devices, 2020, 67, 3435-3441.	3.0	22
9	Forming-Free, Fast, Uniform, and High Endurance Resistive Switching From Cryogenic to High Temperatures in W/AlO$_x$/Al_2O_3/Pt Bilayer Memristor. IEEE Electron Device Letters, 2020, 41, 549-552.	3.9	73
10	Enhancement of DC/AC resistive switching performance in AlOx memristor by two-technique bilayer approach. Applied Physics Letters, 2020, 116, 173504.	3.3	18
11	Analysis of Memristive Quantized Convolutional Neural Network Accelerator with Device Nonideality. , 2020, , .		0